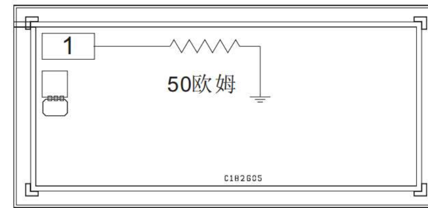
Performance

- Frequency: 8~12GHz
- Input Return Loss: -18dB
- Power Handling: 30W (8ms, 40% D.C)
- Chip size: 1.65*0.8*0.08mm

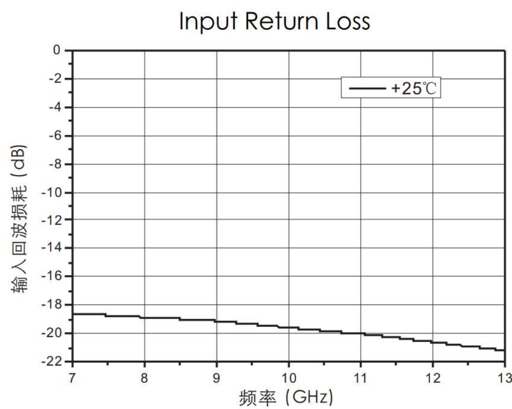
Function Diagram



Electrical Specifications (T_A=+25℃，50Ω system)

Parameter	Min	Typical	Max	Unit
Frequency Range	8~12			GHz
Input Return Loss	-	18	-	dB
Power Handling	-	-	30 (8ms, 40% D.C)	W

Test Curves (Die chip testing)

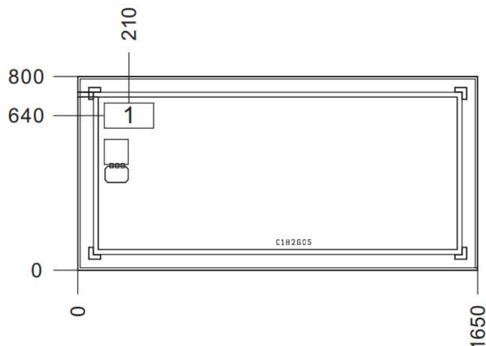


Absolute Max Ratings

Max Handling Power	30W (8ms, 40%)
Junction Temperature	200℃
Sintering Temperature (20 sec, N_2 protection)	320℃
Storage Temperature	-55~+150℃
Operating Temperature	-55~+125℃
Static Protection Grade	Class 1A

ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

Outline Size

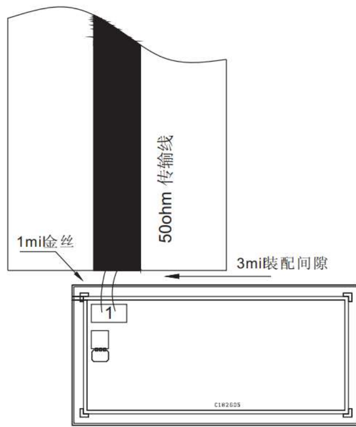


Note:

Unit: um

1. Bottom side is gold plated
2. Bottom side is GND
3. Bonding pads is gold plated: 200*100µm
4. Don't bonding on thru holes
5. Tolerance: ±50um

Assembly Drawing



Typical assemble gap: 0.076~0.152mm (3~6mils)

Bonding Pads Definition

Number	Symbol	Description
1	RFin	RF input port 50 ohm impedance
Bottom	GND	Bottom side of chip must be grounded